

FIG. 1

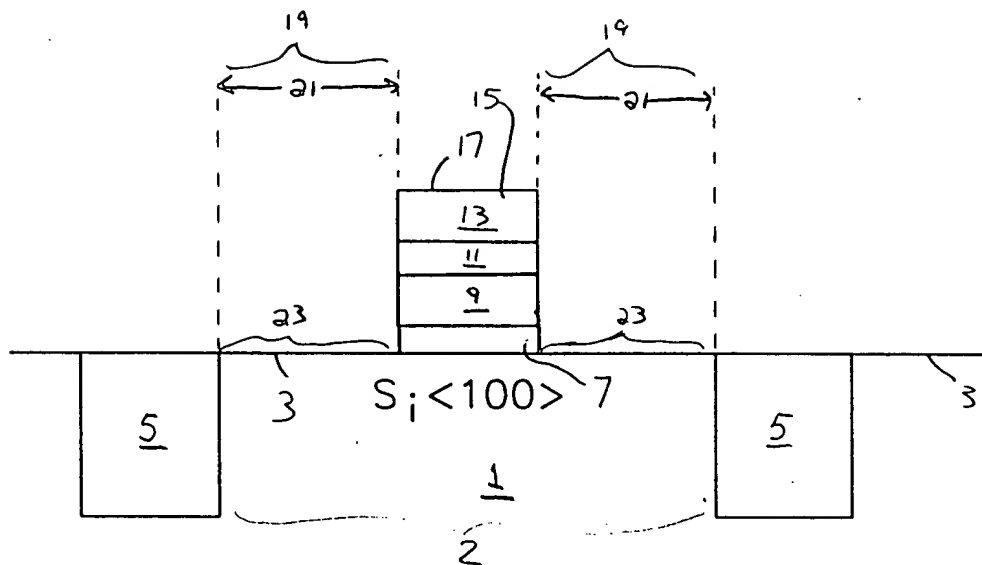


FIG. 2

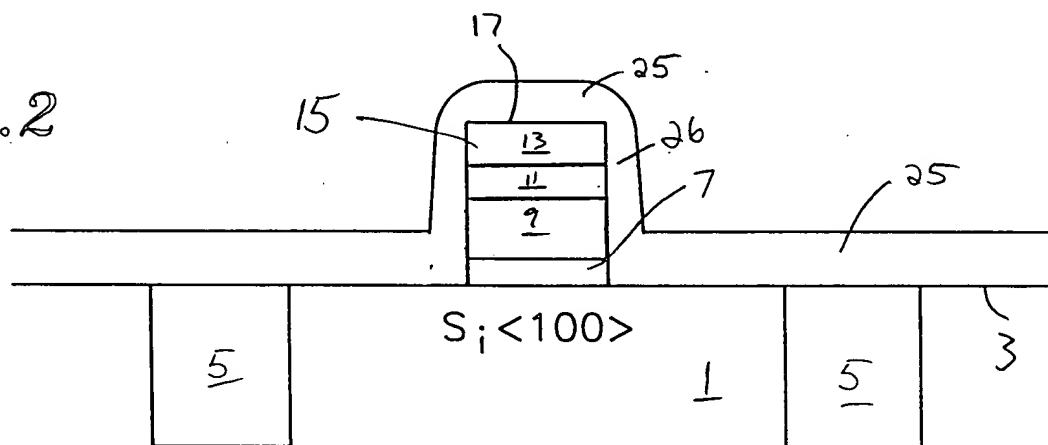
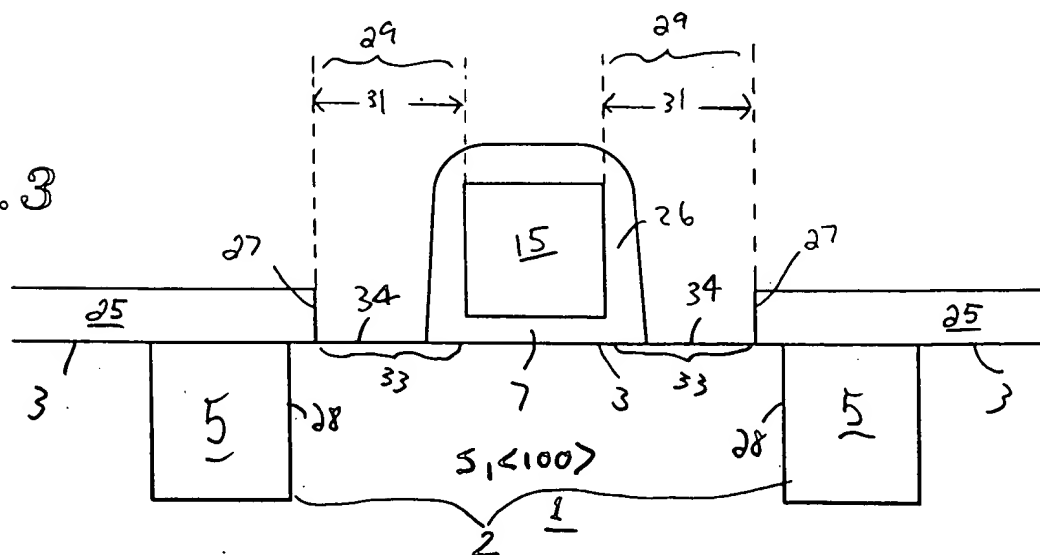


FIG. 3



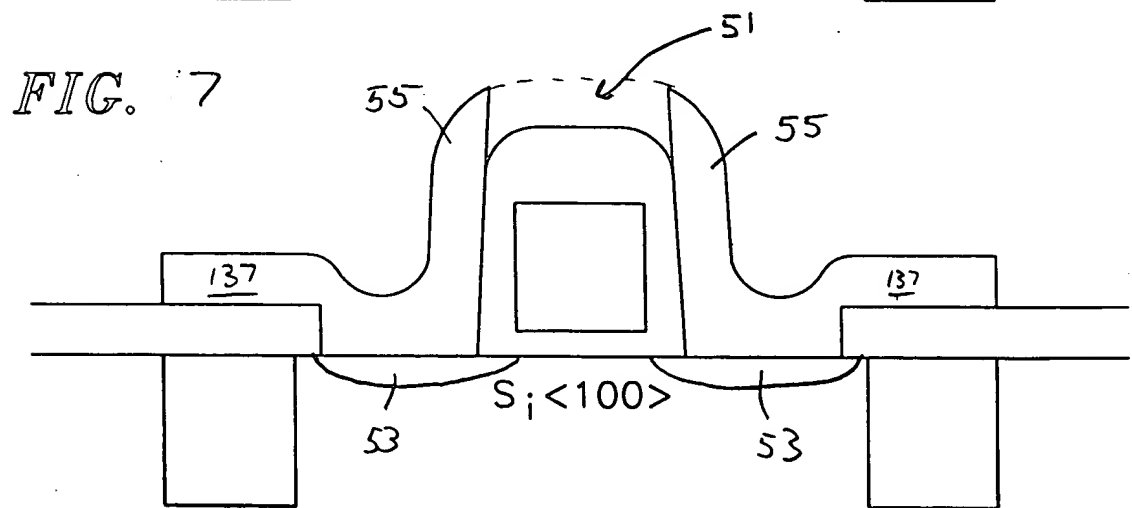
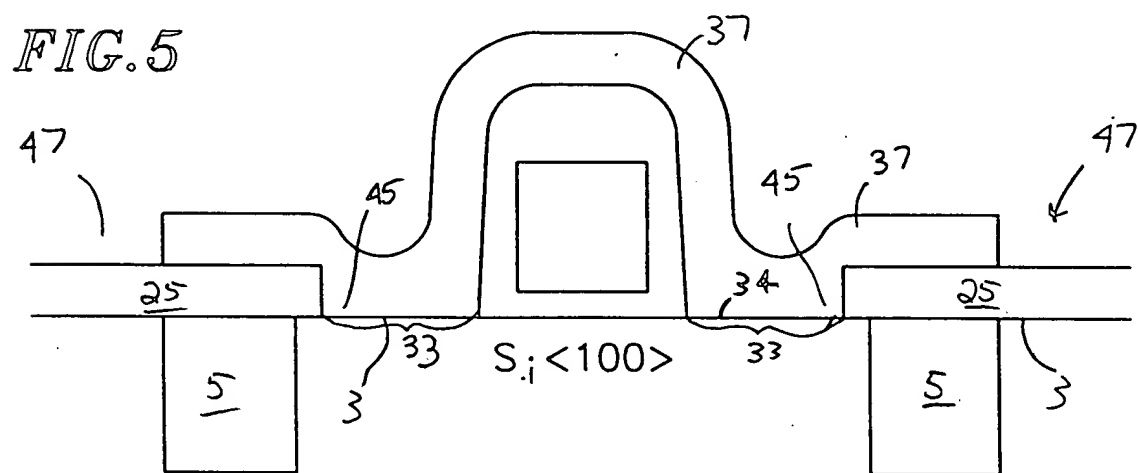
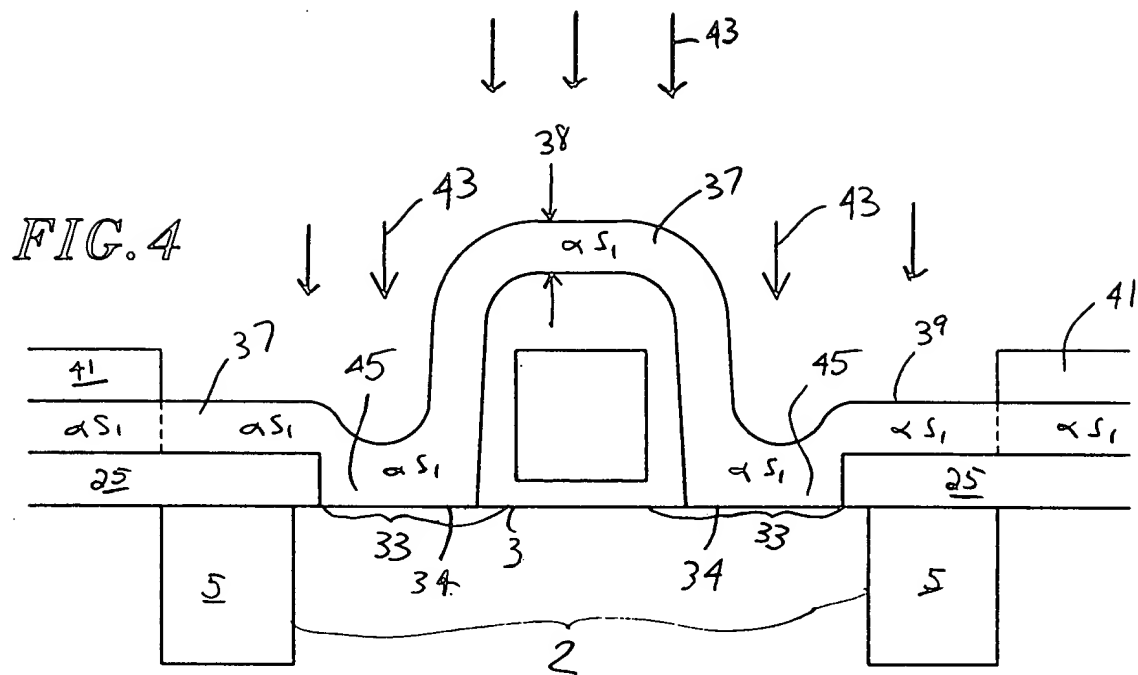


FIG. 6

A cross-sectional view of a semiconductor device. A central square region 15 is surrounded by a U-shaped structure 137. The structure 137 has a top layer 39 and a bottom layer 45. The device is built on a substrate 3. A layer 25 is on top of the substrate, with a layer 26 on top of it. A layer 34 is on top of the layer 25, and a layer 47 is on top of the layer 34. Arrows labeled $h\nu$ 49 indicate incident light. Dashed lines 29 indicate regions below the surface. The substrate is labeled $Si <100>$. Other labels include 5, 53, and 54.

FIG. 8

FIG. 8 is a cross-sectional view of a semiconductor device. The device features a central square region 15 and a central rectangular region 17, which are surrounded by a series of rectangular blocks 59 and 55. The blocks 59 are positioned on top of the blocks 55. The device is divided into two symmetrical halves by a central vertical dashed line 61. Dimensions 67 and 69 are indicated for the top sections, and 63 for the side sections. The substrate 3 is labeled with a silicon crystallographic orientation $\langle 100 \rangle$. Other labels include 5, 53, 55, 57, 59, 61, 63, 67, 69, 71, 137, 15, 17, and 3.